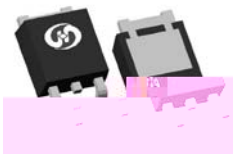
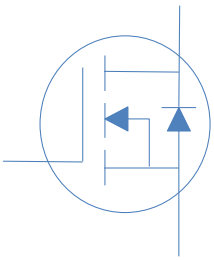
60V N-Ch Power MOSFET

DS(on),typ			Ω
DS(on),typ			Ω





=25 (unless otherwise specified)

		=25		
		=100		
		=25		
Avalanche Energy, Single Pulse	E	=25		
Power Dissipation		=25		W
Operating and Storage Temperature				

Thermal Resistance Junction-Ambient	θ		/W
Thermal Resistance Junction-Case	θ		/W

Electrical Characteristics at T =25 (unless otherwise specified)

Static Characteristics

				typ		
Drain to Source Breakdown Voltage		μ				
Gate Threshold Voltage	GS(th)	μ				
		=25				μ
		=100				
						Ω
	fs					
		Open, f=1MHz				Ω

Dynamic Characteristics

Input Capacitance		=30V, f=1MHz				pF
Output Capacitance						
Reverse Transfer Capacitance						
Total Gate Charge						
Total Gate Charge						
Gate to Source Charge						
Gate to Drain (Miller) Charge						
Turn off Delay Time	d(off)	Ω				
Fall Time	f					

Reverse Diode Characteristics

Diode Forward Voltage		F				
		F /dt=300A/μ				
Reverse Recovery Charge						

Fig 1. Typical Output Characteristics

Figure 2. On-Resistance vs. Gate-Source Voltage

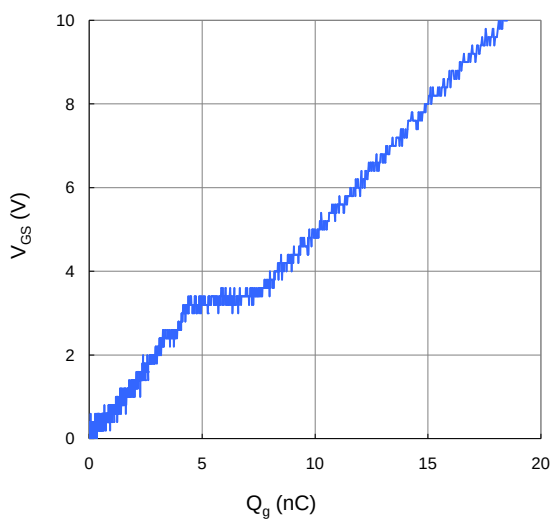
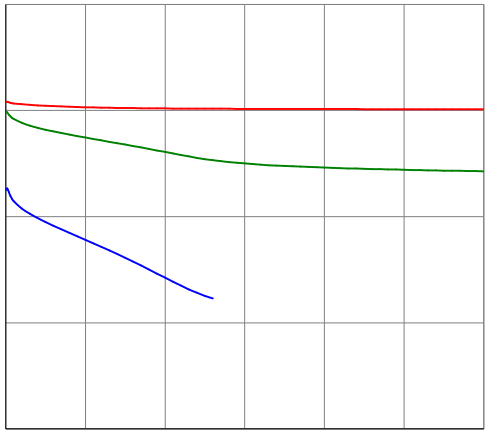
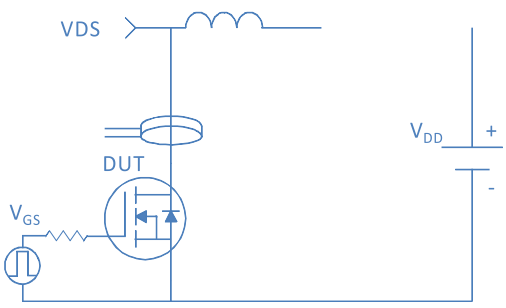
Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage	Figure 8. Typical Capacitance vs. Drain-to-Source Voltage
	

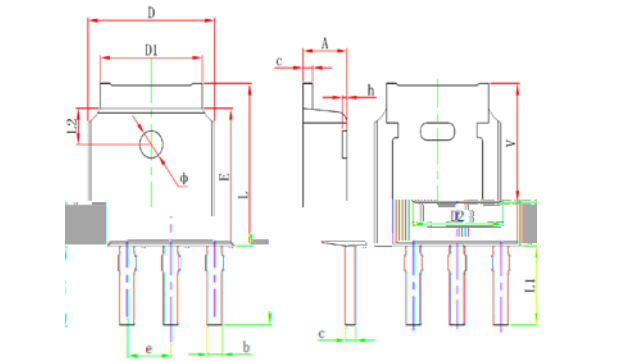
Figure 9. Maximum Safe Operating Area	Figure 10. Maximun Drain Current vs. Case Temperature

Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

Inductive switching Test	

Gate Charge Test	

Uclamped Inductive Switching (UIS) Test	
	



	Dimensions In Millimeters	Dimensions In Inches
[redacted]